



CHENMKO ENTERPRISE CO.,LTD

Lead free devices

**SURFACE MOUNT
NPN Epitaxial Transistor**

VOLTAGE 15 Volts CURRENT 6 Amperes

CHT5564XPT

APPLICATION

- * DC to DC relay drivers,lamp drivers

FEATURE

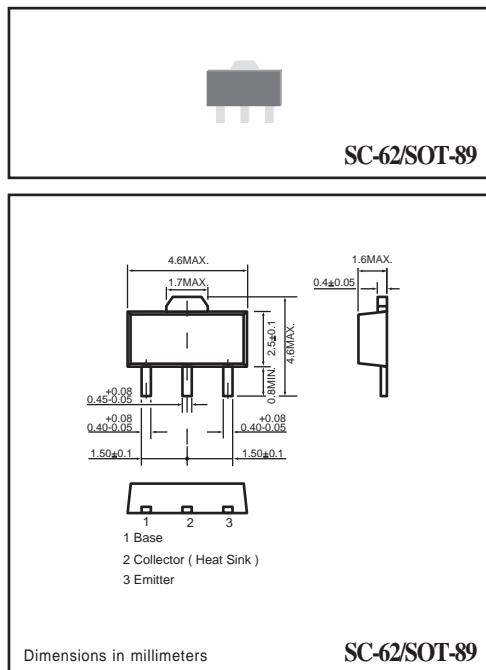
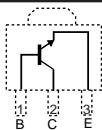
- * Small flat package. (SC-62/SOT-89)
- * Low saturation voltage $V_{CE(sat)}=0.18V$ ($I_C/I_B=1.5A/0.03A$)
- * $PC= 1.3W$ (mounted on ceramic substrate).
- * High saturation current capability.

CONSTRUCTION

- * NPN Cilicon Transistor

MARKING

CIRCUIT



MAXIMUM RATINGS (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

| RATINGS | CONDITION | SYMBOL | MIN. | MAX. | UNITS |
|-------------------------------|--------------------------------------|-----------|------|------|------------------|
| Collector - Base Voltage | Open Emitter | V_{CBO} | - | 20 | Volts |
| Collector - Emitter Voltage | Open Base | V_{CEO} | - | 15 | Volts |
| Emitter - Base Voltage | Open Collector | V_{EBO} | - | 5 | Volts |
| Collector Current DC | | I_C | - | 6 | Amps |
| Peak Collector Current | | I_{CM} | - | 9 | Amps |
| Peak Base Current | | I_{BM} | - | 0.6 | Amps |
| Total Power Dissipation | $T_A \leq 25^\circ\text{C}$; Note 1 | P_{TOT} | - | 1.3 | W |
| Storage Temperature | | T_{STG} | -55 | +150 | $^\circ\text{C}$ |
| Junction Temperature | | T_J | - | +150 | $^\circ\text{C}$ |
| Operating Ambient Temperature | | T_{AMB} | -55 | +150 | $^\circ\text{C}$ |

Note

1. Transistor mounted on ceramic substrate by 40mmX40mmx0.7mm.
2. Measured at Pulse Width 300 us, Duty Cycle 2%.

2006-02

RATING CHARACTERISTIC CURVES (CHT5564XPT)

CHARACTERISTICS (At TA = 25°C unless otherwise noted)

| PARAMETERS | CONDITION | SYMBOL | MIN. | TYPE | MAX. | UNITS |
|--------------------------------------|--|--------------------|------|------|------|-------|
| Collector Cut-off Current | I _E =0; V _{CB} =12V | I _{CBO} | - | - | 0.1 | uA |
| Emitter Cut-off Current | I _C =0; V _{EB} =4V | I _{CEO} | - | - | 0.1 | uA |
| DC Current Gain | V _{CE} =0.5V; Note 1 I _C =5A | h _{FE} | 250 | - | - | |
| Collector-Emitter Saturation Voltage | I _C =1.5A; I _B =0.03A | V _{CEsat} | - | 0.12 | 0.18 | Volts |
| Base-Emitter Saturation Voltage | I _C =1.5A; I _B =0.03A | V _{BEsat} | - | 0.85 | 1.2 | Volts |
| Output Capacitance | I _E =I _B =0; V _{CB} =10V; f=1MHz | C _c | - | 23 | - | pF |
| Transition Frequency | I _C =-0.5A; V _{CE} =2.0V; f=100MHz | f _T | - | 380 | - | MHz |

Note :

1. Pulse test: t_p ≤ 300uSec; δ ≤ 0.02.